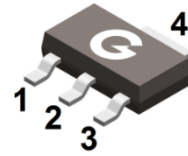
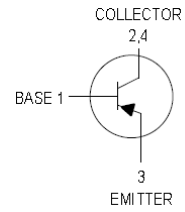


Features

- Low Collector-Emitter saturation voltage $V_{CE(sat)}$ and corresponding low $R_{CE(sat)}$
- High collector current capability
- High collector current gain
- Improved efficiency due to reduced heat generation
- RoHS compliant with Halogen-free

HF



SOT-223

Mechanical Data

- Case: SOT-223
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GT5350R	SOT-223	4000 pcs / Tape & Reel	T5350

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V_{CBO}	-50	V
Collector-Emitter Breakdown Voltage	V_{CEO}	-50	V
Emitter-Base Breakdown Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-3	A
Peak Collector Current ($t_p \leq 1\text{ms}$)	I_{CM}	-6	A
Equivalent On-Resistance	$R_{CE(sat)}$	135	m Ω

Thermal Characteristics

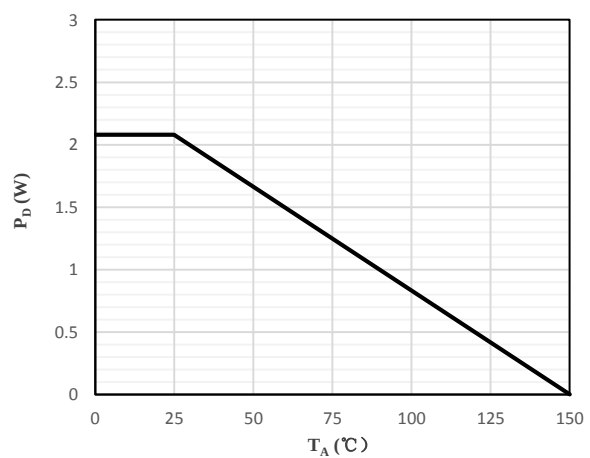
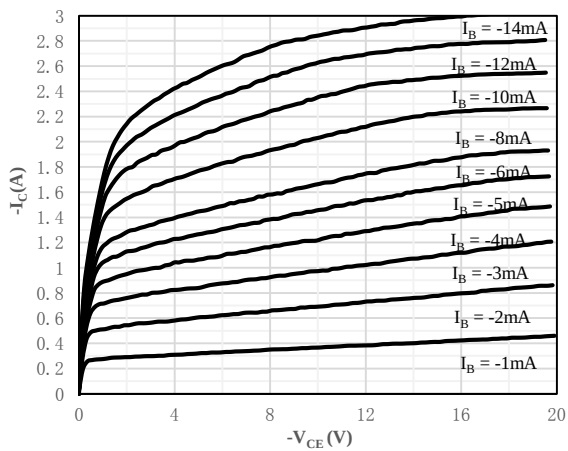
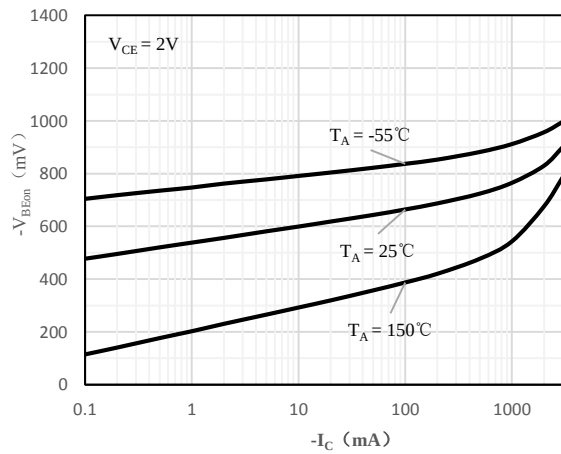
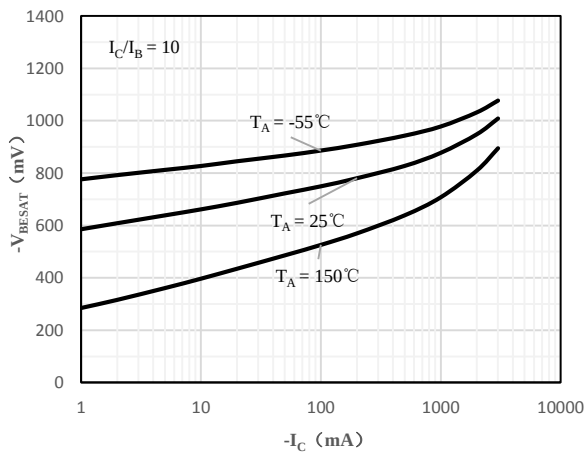
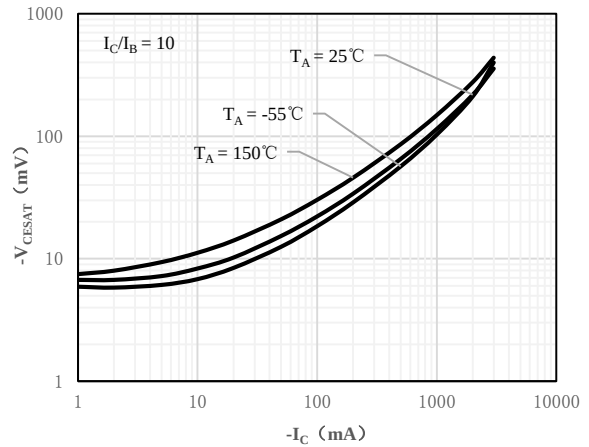
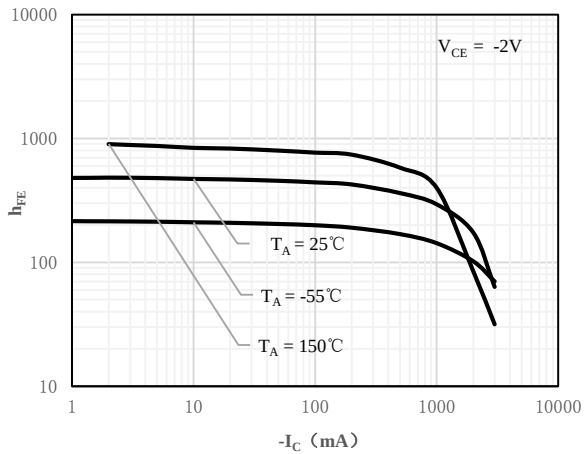
Parameter	Symbol	Value	Unit
Power Dissipation ($T_A = 25^\circ\text{C}$) *1	P_D	2.08	W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	60	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	25	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	20	$^\circ\text{C/W}$
Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$	-	-	-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -100\text{mA}$	200	-	-	-
		$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	200	-	-	-
		$V_{CE} = -2\text{V}, I_C = -1\text{A}$	200	-	-	-
		$V_{CE} = -2\text{V}, I_C = -2\text{A}$	130	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-	-0.09	V
		$I_C = -1\text{A}, I_B = -50\text{mA}$	-	-	-0.18	V
		$I_C = -2\text{A}, I_B = -100\text{mA}$	-	-	-0.32	V
		$I_C = -2\text{A}, I_B = -200\text{mA}$	-	-	-0.30	V
Equivalent On-Resistance	$R_{CE(sat)}$	$I_C = -2\text{A}, I_B = -200\text{mA}$	-	90	135	$\text{m}\Omega$
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -100\text{mA}$	-	-	-1.1	V
Base-emitter Voltage	$V_{BE(on)}$	$I_C = -1\text{A}, V_{CE} = -2\text{V}$	-	-	-1.2	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$ $f = 100\text{MHz}$	100	-	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = I_C = 0$ $f = 1\text{MHz}$	-	-	35	pF

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)



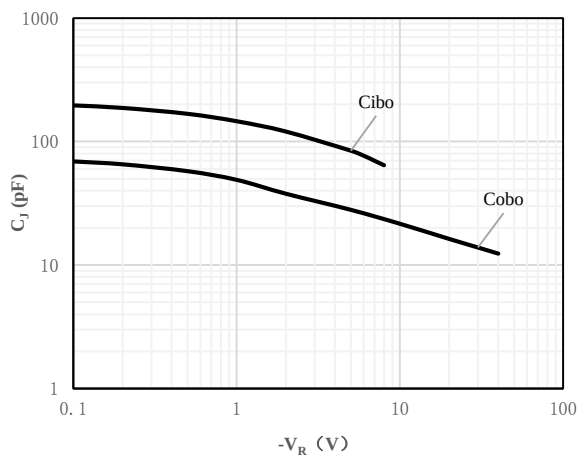
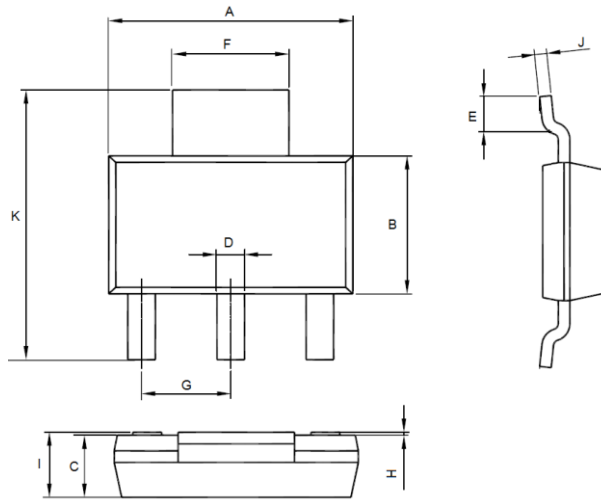


Fig 7 C_J vs. V_R

Package Outline Dimensions (Unit: mm)



SOT-223		
Dimension	Min.	Max.
A	6.10	6.50
B	3.30	3.70
C	1.50	1.70
D	0.66	0.82
E	0.90	1.15
F	2.90	3.10
G	2.20	2.40
H	0.02	0.10
I	1.52	1.80
J	0.20	0.40
K	6.70	7.30

Mounting Pad Layout (Unit: mm)

SOT-223

